



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Makoto KOBAYASHI et al.

Group Art Unit: 3723

Application No.: 09/830,434

Examiner:

H. Shakeri

Filed: April 26, 2001

Docket No.:

109352

For:

POLISHING PAD AND POLISHING METHOD FOR SEMICONDUCTOR WAFER

## **AMENDMENT**

RECEIVED

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

TECHNOLOGY CENTER R3700

Sir:

In reply to the April 29, 2003 Office Action, please amend the above-identified application as follows:

## IN THE CLAIMS:

## Please replace claims 11-13, 20 and 27-31 as follows:

- 11. (Twice Amended) A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a mirror polishing process, wherein a content of zinc oxide (ZnO) included in the polishing pad is 200ppm or less at the ratio of zinc weight relative to the weight of the polishing pad.
- 12. (Twice Amended) A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a finish polishing process, wherein a content of zinc oxide (ZnO) included in the polishing pad is 100ppm or less at the ratio of zinc weight relative to the weight of the polishing pad.

